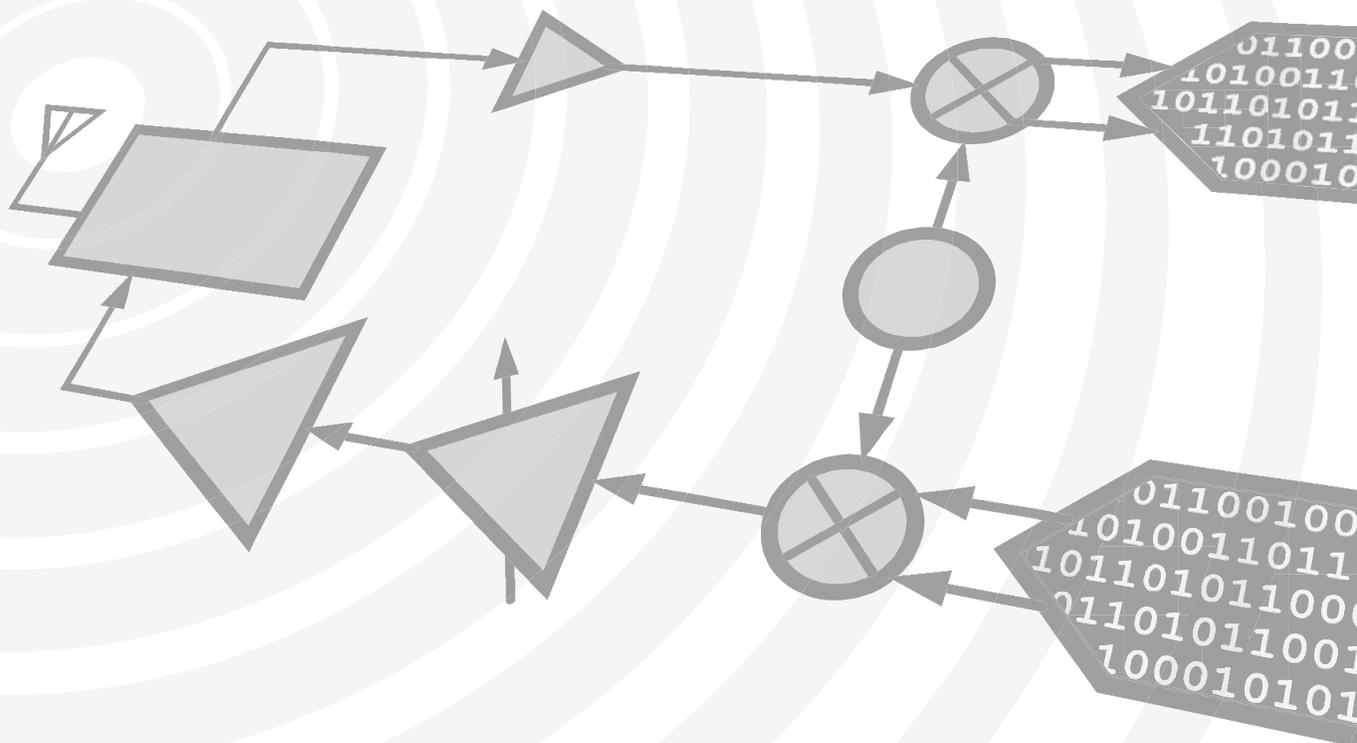


# Analog Devices Welcomes Hittite Microwave Corporation

NO CONTENT ON THE ATTACHED DOCUMENT HAS CHANGED



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## GaAs HEMT MMIC DRIVER AMPLIFIER, 17.5 - 41.0 GHz

### Typical Applications

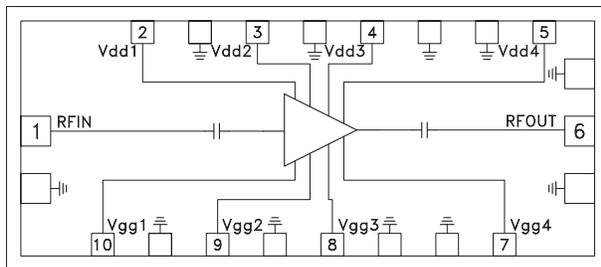
This HMC-AUH256 is ideal for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios
- VSAT
- SATCOM

### Features

- Gain: 21 dB
- P1dB Output Power: +20 dBm
- Wideband Performance: 17.5 to 40 GHz
- Supply Voltage: +5V @ 295 mA
- Small Chip Size: 2.1 x 0.92 x 0.1 mm

### Functional Diagram



### General Description

The HMC-AUH256 is a GaAs MMIC HEMT four stage Driver Amplifier which covers the frequency range of 17.5 to 40 GHz. The chip can easily be integrated into Multi-Chip-Modules (MCMs) due to its small (1.93 mm<sup>2</sup>) size. The HMC-AUH256 offers 21 dB of gain and +20 dBm output power at 1 dB compression from a bias supply of +5V @ 295 mA. The HMC-AUH256 may also be used as a frequency doubler. Detail bias condition to achieve doubler operation.

### Electrical Specifications <sup>[1]</sup>, $T_A = +25^\circ\text{C}$

$V_{dd1} = V_{dd2} = V_{dd3} = V_{dd4} = 5V$ ,  $I_{dd1} + I_{dd2} + I_{dd3} + I_{dd4} = 295mA$  <sup>[2]</sup>

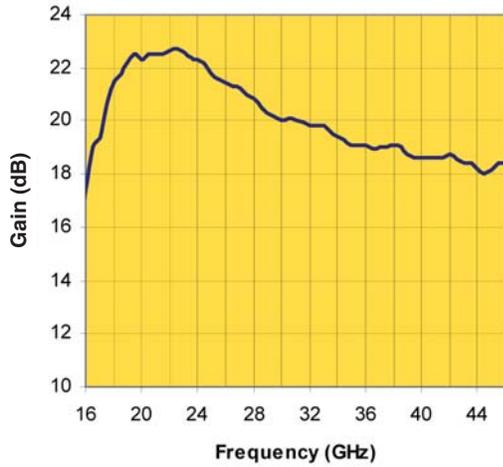
Parameter	Min.	Typ.	Max.	Units
Frequency Range	17.5 - 41			GHz
Gain		21		dB
Input Return Loss		8		dB
Output Return Loss		15 8		dB dB
	20 - 30 GHz			
	30 - 45 GHz			
Output Power for 1 dB Compression		20		dBm
Saturated Output Power		23		dBm
Output IP3		27		dBm
Supply Current ( $I_{dd1} + I_{dd2} + I_{dd3} + I_{dd4}$ )		295		mA

[1] Unless otherwise indicated, all measurements are from probed die

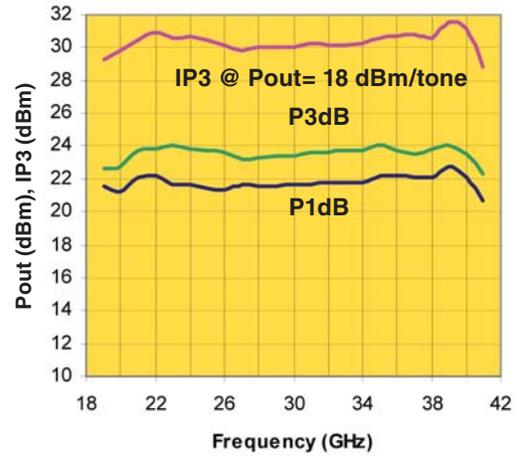
[2] Adjust Vgg1 = Vgg2 = Vgg3 = Vgg4 between -1V to +0.3V (Typ. -0.3V) to achieve  $I_{dd1} = 50\text{ mA}$ ,  $I_{dd2} = 50\text{ mA}$ ,  $I_{dd3} = 75\text{ mA}$ ,  $I_{dd4} = 120\text{ mA}$

**GaAs HEMT MMIC DRIVER  
AMPLIFIER, 17.5 - 41.0 GHz**

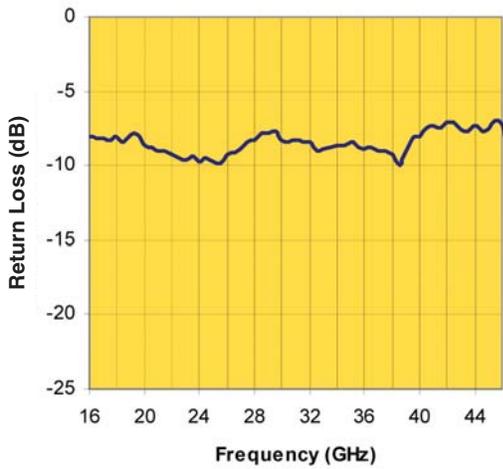
**Linear Gain vs. Frequency**



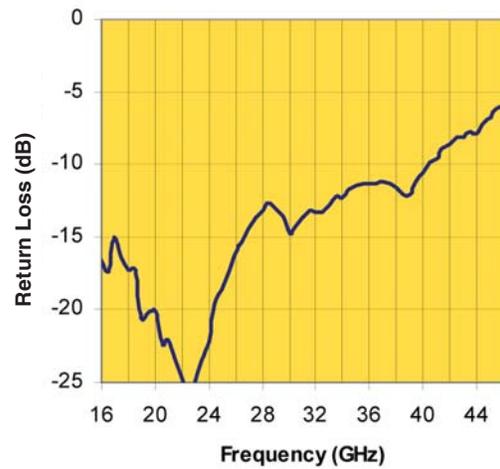
**Fixtured Pout vs. Frequency**



**Input Return Loss vs. Frequency**

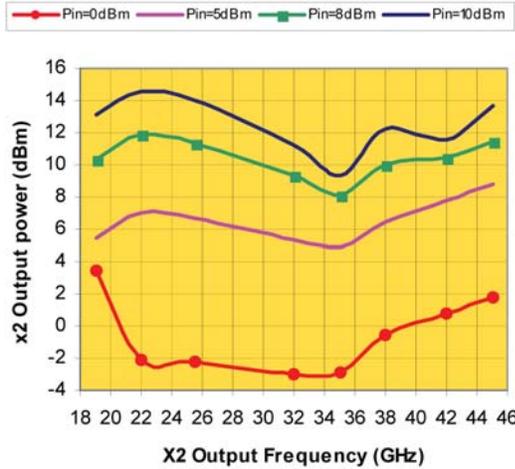


**Output Return Loss vs. Frequency**

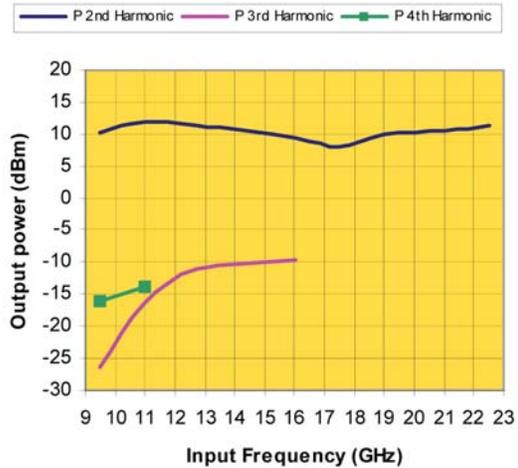


## GaAs HEMT MMIC DRIVER AMPLIFIER, 17.5 - 41.0 GHz

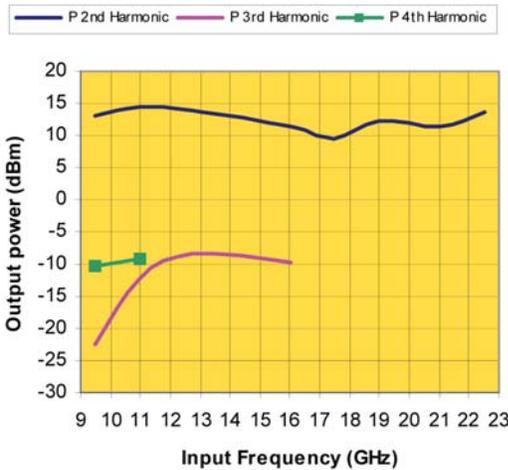
**x2 Pout vs. Frequency (vs Pad)**



**Fixtured Pout vs. Frequency @ Pin= 8 dBm**



**Fixtured Pout vs. Frequency @ Pin= 10 dBm**



**Absolute Maximum Ratings**

Drain Bias Voltage	+5.5 Vdc
RF Input Power	15 dBm
Drain Bias Current (Idd1, Idd2)	62 mA
Drain Bias Current (Idd3)	93 mA
Drain Bias Current (Idd4)	150 mA
Gate Bias Voltage	-1 to +0.3 Vdc
Channel Temperature	180 °C
Thermal Resistance (channel to die bottom)	77.5 °C/W
Storage Temperature	-65 to +150 °C



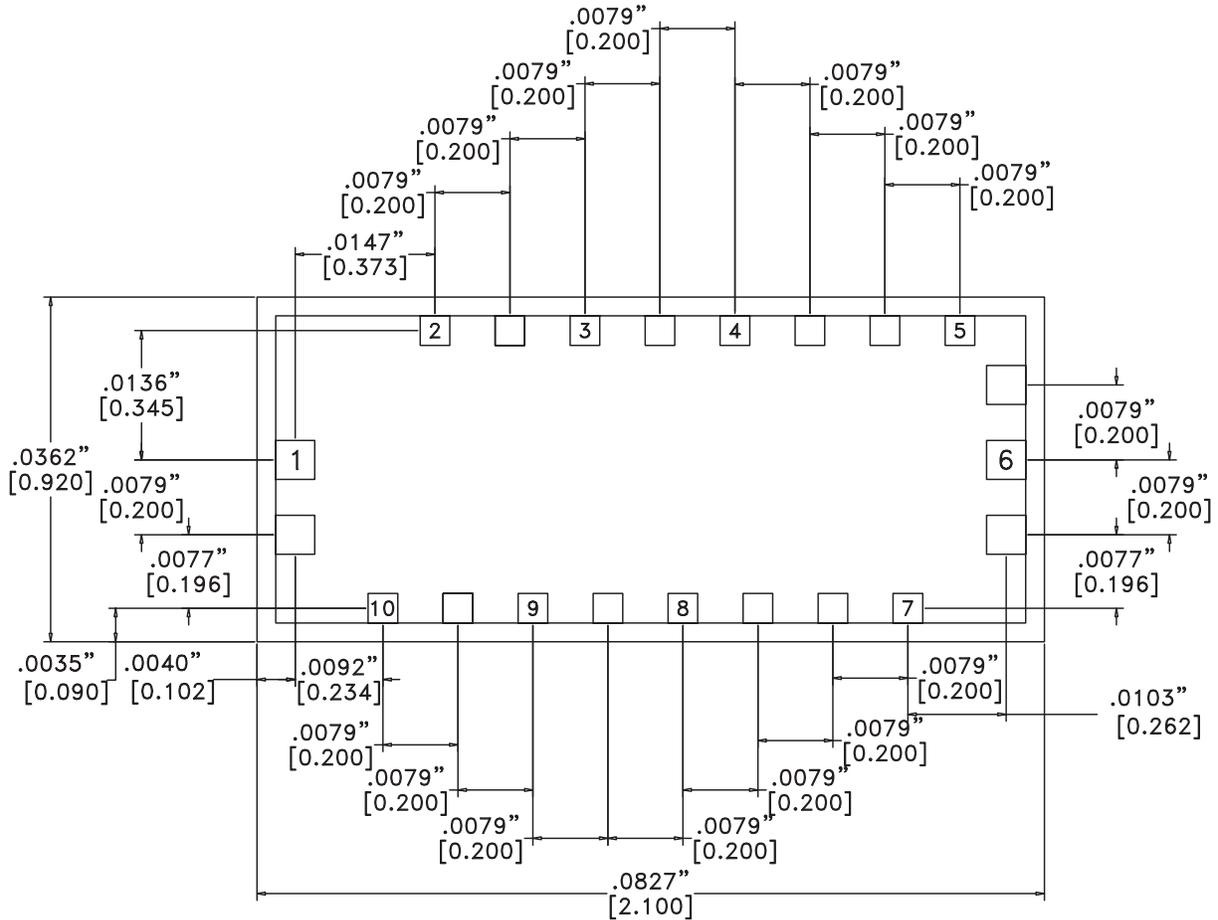
ELECTROSTATIC SENSITIVE DEVICE  
OBSERVE HANDLING PRECAUTIONS

Note: Multiplier Performance Characteristics (Typical Performance at 25°C)  
Vd1= 2V, Vd2= Vd3= Vd4= 5V, Id1= 5mA, Id2+Id3+Id4= 245mA

For price, delivery, and to place orders, please contact Hittite Microwave Corporation:  
20 Alpha Road, Chelmsford, MA 01824 Phone: 978-250-3343 Fax: 978-250-3373  
Order On-line at [www.hittite.com](http://www.hittite.com)

## GaAs HEMT MMIC DRIVER AMPLIFIER, 17.5 - 41.0 GHz

### Outline Drawing



NOTES:

1. ALL DIMENSIONS ARE IN INCHES [MM].
2. TYPICAL BOND PAD IS .004" SQUARE.
3. BACKSIDE METALLIZATION: GOLD.
4. BACKSIDE METAL IS GROUND.
5. BOND PAD METALLIZATION: GOLD.
6. CONNECTION NOT REQUIRED FOR UNLABELED BOND PADS.
7. OVERALL DIE SIZE  $\pm .002$ "

### Die Packaging Information <sup>[1]</sup>

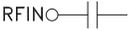
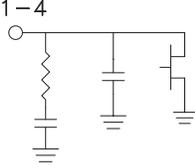
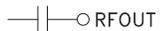
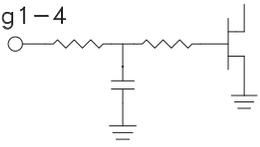
Standard	Alternate
GP-2 (Gel Pack)	[2]

[1] Refer to the "Packaging Information" section for die packaging dimensions.

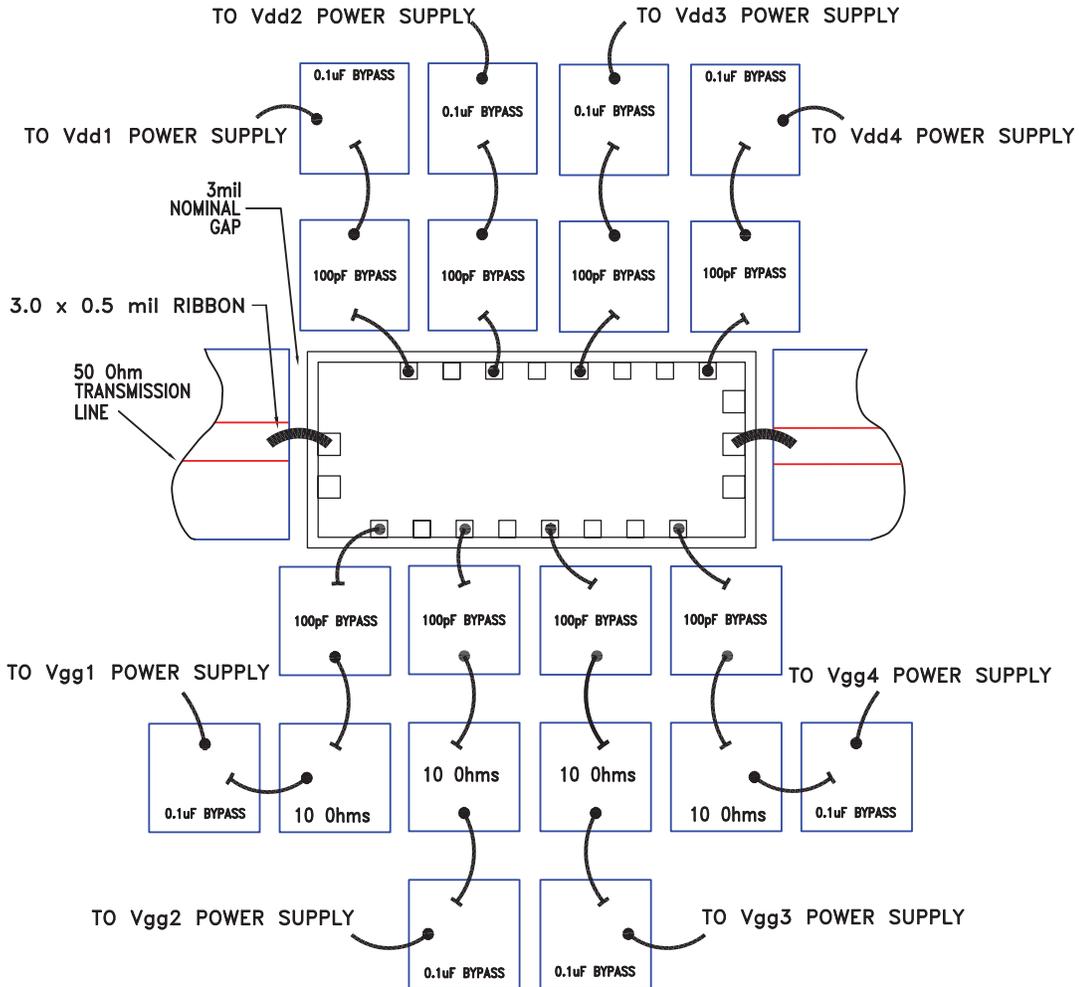
[2] For alternate packaging information contact Hittite Microwave Corporation.

## GaAs HEMT MMIC DRIVER AMPLIFIER, 17.5 - 41.0 GHz

### Pad Descriptions

Pad Number	Function	Pad Description	Interface Schematic
1	RFIN	This pad is AC coupled and matched to 50 Ohms.	RFIN 
2 - 5	Vdd1-4	Power supply voltage for amplifier. See Assembly Diagram for required external components.	Vdd1-4 
6	RFOUT	This pad is AC coupled and matched to 50 Ohms.	 RFOUT
7 - 10	Vgg1-4	Gate control for amplifier. Please follow "MMIC Amplifier Biasing Procedure" application note. See assembly for required external components.	Vgg1-4 
Die Bottom	GND	Die Bottom must be connected to RF/DC ground.	 GND

**Assembly Diagram**



- Note 1: Bypass caps should be 100 pF (approximately) ceramic (single-layer) placed no farther than 30 mils from the amplifier.
- Note 2: Best performance obtained from use of <10 mil (long) by 3 by 0.5mil ribbons on input and output.
- Note 3: Vdd3 can be biased using on-chip pads Vdd3 or Vdd4